

ABSTRACT OF THE DISCLOSURE

In order to provide a reliable surge protective component with a straightforward manufacturing process, first and second buried layers are diffused over the entire inside surfaces of a semiconductor substrate, and first and second base layers are then diffused over the entire inside surfaces of the first and second buried layers. First and second emitter layers are then partially diffused at the inside of the first and second base layers. The peripheries of the first and second emitter layers are then surrounded by first and second moats, the bottoms of which reach the first and second buried layers. A PN junction formed between the first and second base layers and first and second buried layers is then simply a planar junction.

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